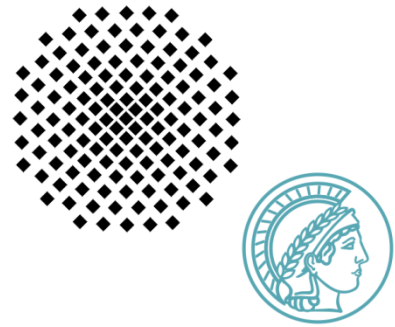


# Stuttgarter Physikalisches Kolloquium

Fachbereich Physik, Universität Stuttgart  
Max-Planck-Institut für Festkörperforschung  
Max-Planck-Institut für Intelligente Systeme

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Dienstag, 09. November 2021

16:15 Uhr

V57.01

Universität Stuttgart, Pfaffenwaldring 57, 70569 Stuttgart-Vaihingen

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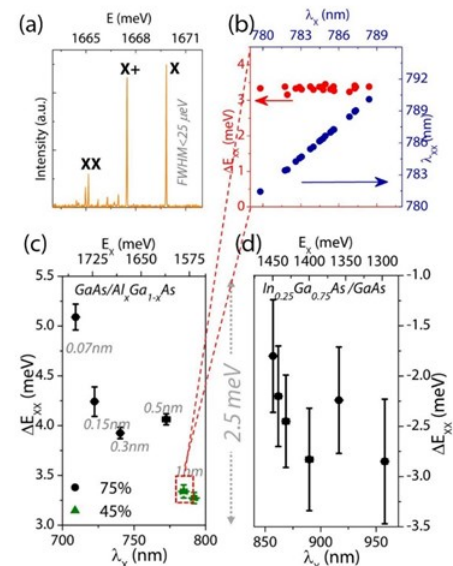
## Why we are moving to GaAs site-controlled pyramidal quantum dots

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### Abstract

Quantum technologies are here to stay. Nevertheless, several issues need to be addressed to make them a reality. In the quantum photonics with quantum dots field several requirements are necessary before practical exploitation. Among them are site-control, emission and “excitonic” uniformity, spectral purity, high QD symmetry, high photon conversion/extraction efficiency, and many specific others. Herein we will navigate through recent achievements of site-controlled InGaAs and GaAs QDs grown by MOVPE in inverted pyramidal recesses. The system is known for its wavelength uniformity, spectral purity, entangled-photon emission quality and potential for practical applications. We will discuss also important recent developments on their control and engineerability, including future directions, and the relevance of resonant pumping strategies. We will also discuss the limitation encountered, and how we hope to overcome them.



**Fig. 1** a) Spectrum of GaAs/Al<sub>0.85</sub>Ga<sub>0.15</sub>As QD with the resolution-limited linewidth below 25 μeV. b) Biexciton binding energy distribution from individual 1 nm GaAs/Al<sub>0.45</sub>Ga<sub>0.55</sub>As QDs. c) Summary of the biexciton binding energy distribution in GaAs/Al<sub>0.45</sub>Ga<sub>0.55</sub>As and GaAs/Al<sub>0.75</sub>Ga<sub>0.25</sub>As QDs. Given points are the average values, and the error bars are standard deviations. d) Summary of the biexciton binding energy distribution in In<sub>0.25</sub>Ga<sub>0.75</sub>As/GaAs QDs for comparison. c) and d) are shown in the same energy range of 2.5 meV for comparison purposes.